

## J. Nano-Science & Technology 분과

2020년 2월 13일(목), 10:45-12:30 / Room H (하트 I, 6층)

### ■ [TH2-J] 뉴로모픽 소자 - I

좌장: 한태희 교수 (한양대학교), 이태우 교수 (서울대학교)

<b>TH2-J-1</b> 10:45-11:15	<b>[초청]</b> <b>Manipulating Grain Boundaries of Metal Halide Perovskite Nanograins</b> Tae-hee Han <i>Division of Materials Science and Engineering, Hanyang University</i>
<b>TH2-J-2</b> 11:15-11:45	<b>[초청]</b> <b>Sensors, Memories and Displays with Nanostructured Ferroelectric</b> Cheolmin Park <i>Department of Materials Science &amp; Engineering, Yonsei University</i>
<b>TH2-J-3</b> 11:45-12:00	<b>One-dimensional (1D) Artificial Multi-synapses based on Ferroelectric Organic Transistor for Wearable Neuromorphic Textile Applications</b> Seonggil Ham <sup>1</sup> , Minji Kang <sup>2</sup> , Seonghoon Jang <sup>1</sup> , Jingon Jang <sup>1</sup> , Sanghyeon choi <sup>1</sup> , Twe-Wook Kim <sup>3</sup> , and Gunuk Wang <sup>1</sup> <sup>1</sup> <i>KU-KIST Graduate School of Converging Science and Technology, Korea University,</i> <sup>2</sup> <i>Functional Composite Materials Research Center and Institute of Advanced Composite Materials, KIST,</i> <sup>3</sup> <i>Department of Flexible and Printable Electronics, Jeonbuk National University</i>
<b>TH2-J-4</b> 12:00-12:15	<b>Implementing Novel Ionic Barrier Layer in Nanoionic Synaptic Transistor for Next Generation Neurocomputing</b> Krishn Gopal Rajput, Revannath Dnyandeo Nikam, Jongwon Lee, and Hyunsang Hwang <i>Center for Single Atom-based Semiconductor Device and Department of Material Science and Engineering, POSTECH</i>
<b>TH2-J-5</b> 12:15-12:30	<b>Sodium Ion Based Three-terminal Synapse Device with Near Ideal Synaptic Behavior and Improved Retention for Neuromorphic Systems</b> Kyumin Lee, Jongwon Lee, Revannath Dnyandeo Nikam, Seongjae Heo, and Hyunsang Hwang <i>Center for Single Atom-based Semiconductor Device, and also Department of Materials Science and Engineering, POSTECH</i>